

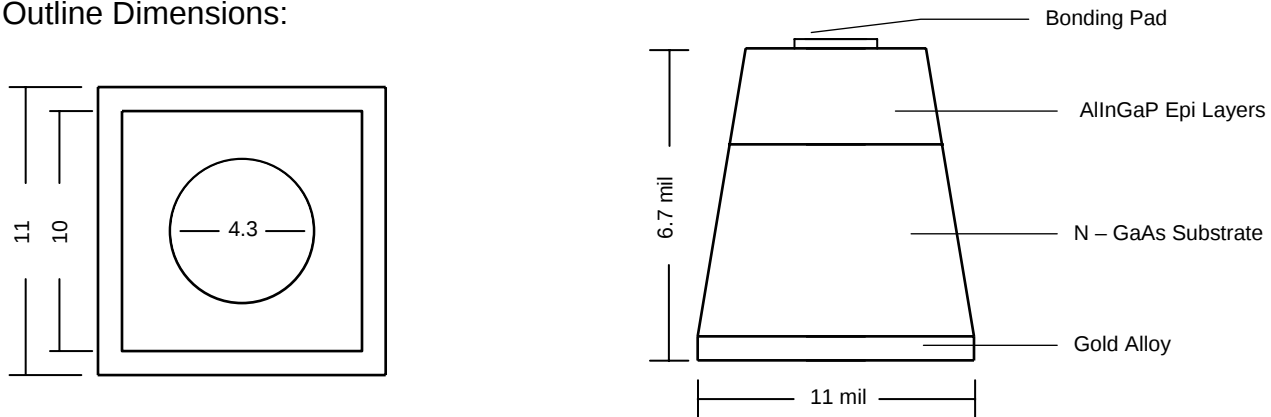
TCE11UYG



❖ Features:

- AlInGaP/GaAs LED Chips
- High luminous intensity
- Low driving current
- Indoor/Outdoor applications
- 100% probing test

❖ Outline Dimensions:



❖ Physical Structure:

Chip dimensions		Chip size	9 mil x 9 mil	230 μ m x 230 μ m
		Thickness	6.7 mil	170 μ m
		Emission area	8 mil	203 μ m
		Bonding pad	3.8 mil	96 μ m
Electrode	Top	P (anode)	Aluminium (Gold optional)	
	Backside	N (cathode)	Gold alloy	

❖ Electro-Optical Characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 10\mu A$	1.40	-	-	V
		$I_F = 20mA$	-	2.05	2.40	
Wavelength	λ_p	$I_F = 20mA$	567	573	575	nm
	λ_d			571		
Spectral width at half height	$\Delta\lambda$	$I_F = 20mA$	-	15	-	nm
Reverse Voltage	I_R	$V_R = 10V$	-	-	100	μA
Luminous Intensity	I_v	$I_F = 20mA$	40	-	-	mcd
			50	-	-	
			60	-	-	